

DESCRIPTION

The UC2635 is USB adapter emulators with automatic host charger identification circuitry for USB dedicated chargers.

The devices integrated automatic USB charger identification circuit allow mobile power supply, In-Car charger, USB wall adapters, travel chargers, and other dedicated chargers to identify themselves as a USB dedicated charger to USB devices, like Apple charger to Apple products, Samsung charger to Samsung Galaxy Tab & Phone, and BC1.2 charger to HTC, SONY, LG, BlackBerry, Lenovo, Coolpad, ZTE, Huawei and other legacy D+/D- short detection devices.

The devices feature a control input that allows for charger mode selection. The UC2635 supports both Apple 2.1A, Galaxy 2.0A and USB BC1.2 compliant devices in SEL Floating or SEL Pull-High and Apple 2.1A, Galaxy 2.0A and USB BC1.2 compliant devices in SEL Pull Down.

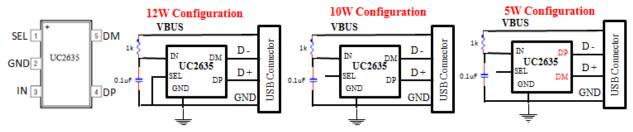
FEATURES

- 4.5V~5.5V Single Supply Operation.
- SEL Pin Control Charger Mode.
- Automatic USB charger Identification Circuit.
- Support Apple® Devices fast charging. (Apple® 2.1A / 2.4A mode)
- Support Samsung Galaxy Tab Devices fast Charging.
- Support BC1.2 & YD/T 1591-2009 Charging Spec.
- Available in SOT23-5 Package.

APPLICATIONS

Mobile Power Supply In-Car Charger USB Wall Adapter Travel Charger

UC2635 SOT23-5 PACKAGE and SIMPLIFIED APPLICATION



ORDING INFORMATION

Part Number	Package Type	Package Qty	Op Temp(°C)
UC2635	SOT23-5	3000	-40~85



ABSOLUTE MAXIMUM RATINGS (1)

Over recommended operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT		
supply voltage range	IN	-0.3	6	V	
Input voltage range	DP,DM	-0.3	5.8		
Continuous output sink current	DP input current, DM input current		35	A	
Continuous output source current	DP output current, DM output current		35	mA	
ESD rating, Human	IN		2	14) /	
Body Model (HBM)	DP, DM		4	kV	
ESD rating, Charging Device Model (CDM)			500	V	
Operating Junction Temperature	T _J	-40	125	°C	
Storage Temperature Range	T _{stg}	-65	150	-0	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	THERMAL METRIC				
θ_{JA}	Package thermal impedance ⁽¹⁾	180	°C/W		

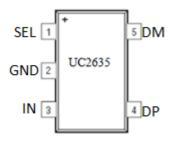
⁽¹⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

RECOMMENDED OPERATING CONDITIONS

PARAMETER				UNIT
V _{IN}	Input voltage of IN	4.5	5.5	V
V _{DP/DM}	DP/DM data line input voltage		5.5	V
I _{DP/DM}	Continuous sink/source current		±10	mA
T _J	Operating Junction Temperature	-40	125	°C



PINOUT

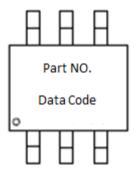


PIN FUNCTIONS

NO.	NAME	TYPE ⁽¹⁾	DESCRIPTION
1	SEL	I	Mode selection pin. SEL = FLOAT or "1" is 10W mode, SEL = "0" is 12W mode.
2	GND	G	Ground connection
3	IN	P/I	Power supply/Input voltage connected to Power Switch; connect a 1 µF or greater ceramic capacitor from IN to GND as close to the IC as possible
4	DP	O/I	DP date line to connector, output for hand-shake voltage to portable equipment, high impedance while disabled
5	DM	O/I	DM data line to connector, input for hand-shake voltage from portable equipment high impedance while disabled

(1) G = Ground, I = Input, O = Output, P = Power

MARK INFORMATION





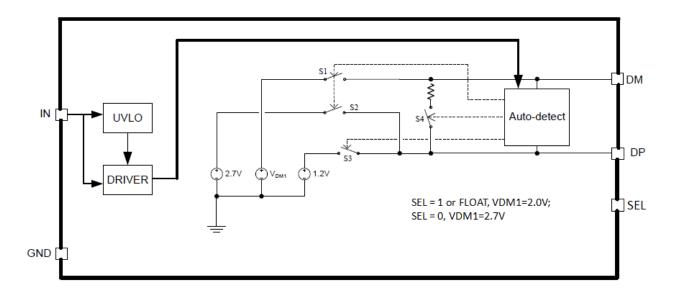
ELECTRICAL CHARACTERISTICS

Conditions are -40°C \leq (T_J =T_A) \leq 125°C and 4.5 V \leq V_{IN} \leq 5.5 V unless otherwise noted. Typical value is at 25°C. All voltages are with respect to GND unless otherwise noted.

-	ARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
UNDERVOLTAGE I	LOCKOUT		•		<u>'</u>	
V _{UVLO}	IN rising UVLO threshold voltage		3.9	4.1	4.3	V
	Hysteresis			100		mV
SUPPLY CURRENT	Γ		-			
I _{IN}	IN supply current			160	250	μA
BC 1.2 DCP MODE	(SHORT)		-		<u>'</u>	
R _{DPM_SHORT}	DP / DM shorting resistance			125	200	Ω
R _{DCHG_SHORT}	Resistors connected DP /DM to GND after hand-shaking			200	400	kΩ
V _{DPL_TH_DETACH}	DP low threshold while detaching BC1.2 devices		310	330	350	mV
V _{DPL_TH_DETACH_HYS}	hysteresis			50		mV
IPAD MODE 2.1A N	lode (SEL=1 or Floating)					
V_{DP_IPAD}	DP output voltage		2.55	2.7	2.85	V
V_{DM_IPAD}	DM output voltage		1.9	2.0	2.1	V
R _{DP_IPAD}	DP output impedance	I _{DP} = -5uA	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	I _{DM} = -5uA	20	30	40	kΩ
IPAD MODE 2.4A N	lode (SEL=0)					
V_{DP_IPAD}	DP output voltage		2.55	2.7	2.85	V
V_{DM_IPAD}	DM output voltage		2.55	2.7	2.85	V
R _{DP_IPAD}	DP output impedance	I _{DP} = -5uA	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	I _{DM} = -5uA	20	30	40	kΩ
Galaxy Tab MODE						
V _{DP_GAL}	DP output voltage		1.1	1.2	1.3	V
V _{DM_} GAL	DM output voltage		1.1	1.2	1.3	v
RDP_GAL	DP output impedance	I _{DP} = -5uA	80	105	130	1.0
Rdm_gal	DM output impedance	I _{DM} = -5uA	80	105	130	kΩ



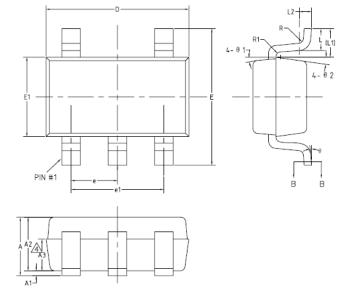
FUNCTIONAL BLOCK DIAGRAM





PACKAGE INFORMATION

SOT23-5



BASE METAL SECTION B-B

NOTES:

ALL DIMENSIONS REFER TO JEDEC STANDARD MO-178 AA DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX		
Α	-	-	1.45		
A1	0	_	0.15		
A2	0.90	1.10	1.30		
A3	0.60	0.65	0.70		
b	0.39	-	0.49		
b1	0.38	0.40	0.45		
С	0.12	-	0.19		
c1	0.11	0.13	0.15		
D	2.82	2.92	3.02		
E	2.70	2.90	3.10		
E1	1.52	1.62	1.72		
е	0.85	0.95	1.05		
e1	1.80	1.90	2.00		
L	0.35	0.45	0.60		
L1		0.59REF			
L2	0.25BSC				
R	0.10	_	1		
R1	0.10	-	0.25		
θ	0,	_	8.		
θ 1	7*	6.	11*		
θ 2	8*	10*	12°		